

ABSTRACT

In an insulated gate semiconductor device (1) having an N^- type base region (11), P^+ type collector regions (12), P type base regions (13), and N^+ type emitter regions (14), an N^+ type collector-short region (15) which extends toward the N^- type base region (11) 5 farther than the P^+ type collector regions (12) is formed in the lower surface of the N^- type base region (11), and a P^+ type semiconductor region (16) is formed between the N^+ type collector-short region (15) and the N^- type base region (11).